Schottky barrier diode

RB411D

●Applications

Low power rectification
For switching power supply

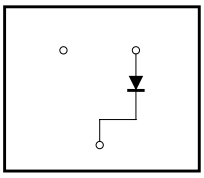
●Features

1) Small surface mounting type. (SMD3)
2) Low V_F. (V_F=0.43V Typ. at 0.5A)
3) High reliability.

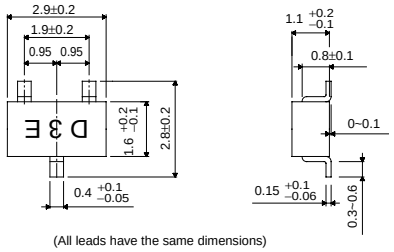
●Construction

Silicon epitaxial planar

●Circuit



●External dimensions (Units : mm)



(All leads have the same dimensions)

ROHM : SMD3
EIAJ : SC-59
JEDEC : SOT-346

●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	20	V
Mean rectifying current	I_O	0.5	A
Peak forward surge current *	I_{FSM}	3	A
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	−40~+125	°C

* 60Hz for 1 ∿

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{F1}	–	–	0.3	V	I_F=10mA
Forward voltage	V_{F2}	–	–	0.5	V	I_F=500mA
Reverse current	I_R	–	–	30	μA	V_R=10V
Capacitance between terminals	C_T	–	20	–	pF	V_R=10V, f=1MHz

Note) sensitive product handling required.

●**Electrical characteristic curves** (Ta = 25°C)

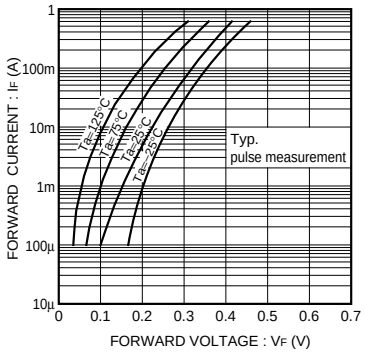


Fig. 1 Forward characteristics

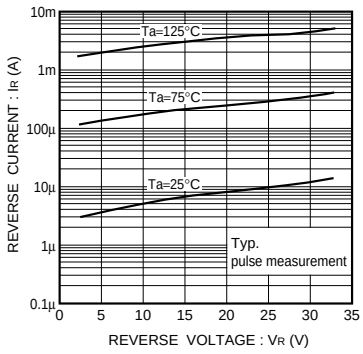


Fig. 2 Reverse characteristics

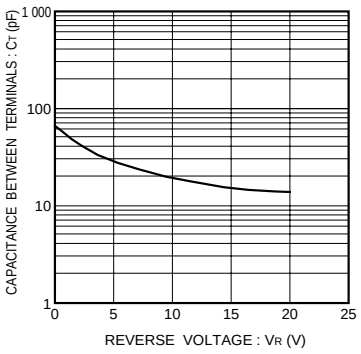


Fig. 3 Capacitance between terminals characteristic